

## Photoemission study of twisted monolayers and bilayers of WSe<sub>2</sub> on graphite substrates

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Using microfocused angle-resolved photoemission spectroscopy we investigated microstructures containing regions of single-layer (SL) and bilayer (BL) WSe<sub>2</sub> on graphite substrates at different twist angles between SL WSe<sub>2</sub> and graphite and within the BL WSe<sub>2</sub>. Fermi level electrons emitted from the graphite are sharply focused near their  $K_{gr}$  points in the Brillouin zone, and, when passing through the WSe<sub>2</sub>, get diffracted to form band replicas readily observed in experimental Fermi surface maps from twisted SL WSe<sub>2</sub>/graphite. We investigated two twisted BL WSe<sub>2</sub> at twist angles  $\sim 28^\circ$  and  $\sim 10^\circ$  and found no evidence of hybridization gaps at the interlayer band-crossing points, that could be precursors of the flat bands at smaller twist angles. Similarly, no such gaps were found for SL WSe<sub>2</sub>/graphite. Experimental results are complemented by theoretical density functional theory calculations, which suggest that a formation of hybridization gaps in the WSe<sub>2</sub>/graphene (which approximates the experimental WSe<sub>2</sub>/graphite system) sensitively depends on the WSe<sub>2</sub> band character at the crossing point with the graphene Dirac band.

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### I. INTRODUCTION

Van der Waals materials, such as transition metal dichalcogenides (TMDCs), emerged as an intriguing class of layered compounds that exhibit dramatic changes in the electronic properties when the film thickness is reduced down to a single layer [1]. Additionally, assembling these individual layers with different electronic properties facilitates the idea of realizing artificial stacks of solids, the so-called *van der Waals heterostructures* (HSs) [2]. The HS's design enables tailoring the band alignment at various semiconductor interfaces [3,4] into different types of heterojunctions [5–10]. This approach of material design comprises superposition of two crystal lattices with the same or different atomic registries, which leads to the construction of a long-range periodic superlattice. It often gives rise to a periodic moiré pattern that can emerge either from the different lattice constants or from the twist angle. In particular, the twist angle  $\theta$  between such layers provides an adjustable degree of freedom as compared to the conventional materials. The potential resulting from the moiré pattern influences lattice electrons, leading to novel emerging properties [11].

Following the prediction of Bistritzer and MacDonald [12], and the demonstration of the gate-controlled superconductivity in twisted bilayer graphene (TBG) [13], similar models have been reported for TMDCs [14–16] predicting fascinating electron correlations and topologies in their twisted bilayer structures. In particular, Wang *et al.* [6] reported experimental evidence of low-energy flat bands in twisted bilayer WSe<sub>2</sub>, with signatures of collective phases in transport measurements for twist angles  $\theta$  between  $4^\circ$  and  $5.1^\circ$ . Recently, Kundu *et al.* [17] have examined the formation of flat bands in twisted BL WSe<sub>2</sub> for twist angles down to  $2.28^\circ$ .

Angle-resolved photoemission (ARPES) is the method of choice for electronic band structure mapping. However, applying this technique to microflakes is challenging, due to their small size, and has become possible only within the last decade following the development of microfocused ARPES (microARPES) techniques [18]. Recent microARPES works on TMDC microflakes have reported band replicas due to scattering on the moiré reciprocal vectors [19], on the moiré potential [20], and  $\theta$ -dependent hybridization and superlattice effects [21]. Furthermore, recently microARPES provided evidence for flat bands in the magic-angle twisted bilayer graphene [22,23].

In this work, we investigate two types of sample structures: twisted single-layer (SL) WSe<sub>2</sub>/graphite and twisted bilayer

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(BL)  $\text{WSe}_2/\text{graphite}$  fabricated by mechanical exfoliation technique. These structures exhibit two types of twist angles: between the graphite and  $\text{WSe}_2$  and between the top and bottom layers of  $\text{WSe}_2$ . In BL structures, previously reported double bands at  $\Gamma$  points near the valence band maximum (VBM) [3,24] manifest the interlayer hybridization. They are also confirmed in our theoretical calculations of twisted BL  $\text{WSe}_2$ , where the splitting of the double bands decreases for the twisted layers, as compared to the aligned BL. Aside from these signatures, in the region of interest near the VBM, the spectra appear as an incoherent sum from the two layers. At our experimental resolution we observe no signs of hybridization gaps that could be precursors of flat bands for smaller twist angles.

In the twisted SL  $\text{WSe}_2/\text{graphite}$  structures, the electrons emitted from the graphite  $\pi$  bands scatter in the SL  $\text{WSe}_2$  layer leading to the emergence of multiple copies [19,25] which reflect the trigonal symmetry of a SL  $\text{WSe}_2$ . We argue that this effect is related neither to the hybridization between SL  $\text{WSe}_2$  and graphite, nor to the formation of the moiré lattice, and would be present also for noninteracting layers.

We also performed calculations of the SL  $\text{WSe}_2/\text{graphene}$  that approximate the experimental  $\text{WSe}_2/\text{graphite}$  system. We found that for the topmost valence bands the magnitude of the hybridization gaps between the graphene and  $\text{WSe}_2$  in the vicinity of the  $K$  point depends on twist angle. This effect is likely related to the out-of-plane orbital contribution to the  $\text{WSe}_2$  band character at the band-crossing points, and to the relative alignment of the  $\text{W } d_{x^2-y^2}$  and graphene  $p_z$  orbitals with respect to the position in the Brillouin zone.

## II. METHODS

### A. Sample preparation

Samples were prepared by using the dry transfer technique, as reported in [26]. Highly oriented pyrolytic graphite (HOPG) was exfoliated on  $n$ -doped Si substrate by scotch tape method to obtain flakes with thicknesses ranging from 10 to 40 nm. The graphite flakes serve the purpose of the atomically flat conductive substrate for the flake sample structures. Before the transfer,  $n$ -doped Si substrates were ultrasonically cleaned in isopropanol, acetone, and ionized water solvents to remove the native oxide, at an interval of 15 min in each solvent, and then dried with a nitrogen gun. The bulk layered  $\text{WSe}_2$  crystal was exfoliated with a scotch tape to obtain atomically thin flakes. These two-dimensional (2D)  $\text{WSe}_2$  flakes were transferred onto the polydimethylsiloxane (PDMS) stamp, which was adhered to the glass slide to ease its handling for further processing. The transparent stamp allows us to identify single-layer  $\text{WSe}_2$  flakes through the contrast observed using the transmission mode under an optical microscope.

Once we identified a single layer of  $\text{WSe}_2$  on the PDMS stamp positioned on the surface of the glass slide, we attached it on the three-axis manipulator facing upside down. Next, the exfoliated thick graphite flake on  $n$ -doped Si substrate has been mounted on the XYZ stage using vacuum and the substrate was heated up to  $75^\circ\text{C}$ – $100^\circ\text{C}$ , facilitating the transfer process. By carefully aligning the transparent PDMS stamp,

the  $\text{WSe}_2$  flakes were then transferred at a submicrometer resolution over a desired location on the thick graphite flake. We repeated the same process for transferring the second monolayer of  $\text{WSe}_2$  on top of  $\text{WSe}_2/\text{graphite}/n\text{-Si}$ . This way we obtained both SL and BL structures of  $\text{WSe}_2$  on  $\text{graphite}/n\text{-Si}$  since both SL and BL parts are present in each microstructure. With this process, we prepared three microstructures (samples *A*, *B*, and *C*) with different twist angles between their constituent layers.

### B. Spatially resolved angle-resolved photoemission spectroscopy

Samples *A* and *B* were transported to the Microscopic and Electronic Structure Observatory (MAESTRO) at the Advanced Light Source. The samples were annealed at  $300^\circ\text{C}$  for several hours prior to the measurement in order to desorb adsorbates. The microARPES measurements were performed at the *nanoARPES* end station at a base pressure lower than  $5 \times 10^{-11}$  mbar at primarily a photon energy of 147 eV and using a focusing capillary that produced a beam spot size of approximately  $1 \mu\text{m}$  [27]. The data were collected using a modified Scienta R4000 hemispherical electron analyzer. All measurements were carried out at 40 K.

Additional microARPES measurements were conducted at the ANTARES beamline of the Soleil synchrotron facility on sample *A*. Before the measurements, we followed the same sample preparation procedures as those used at MAESTRO beam line. At ANTARES, by the utilization of Fresnel zone plate optics, the beam was focused to  $\sim 0.6 \mu\text{m}$ . All of the measurements were carried out at  $h\nu = 100$  eV with  $p$ -polarized light and at 100 K.

Further experiments on atomically thin SL  $\text{WSe}_2/\text{graphite}$  microstructure (sample *C*) were performed at the NanoESCA beam line of Elettra, Trieste, with beam spot size of 10–15  $\mu\text{m}$  using a modified FOCUS NanoESCA momentum microscope. Before the experiments, the sample was subjected to the same preparation processes as at the other beam lines. A homogeneous region on the sample surface was identified by using the photoemission electron microscopy (PEEM) in real space with high-pressure Hg lamp as an excitation source. Moreover, unlike traditional ARPES setups, momentum microscope scans the complete half-space emission without rotating the sample and enables high linearity in the  $k_{\parallel x}$  vs  $k_{\parallel y}$  maps. All measurements at the NanoESCA were taken at 80 K using  $h\nu = 40$  eV  $p$ -polarized light.

### C. Density functional theory calculations

To investigate the twisted SL  $\text{WSe}_2/\text{graphene}$  and twisted BL  $\text{WSe}_2$ , we performed density functional theory (DFT) calculations using the VASP code [28,29]. Projector augmented wave potentials [30] were employed to describe the valence electrons, the electronic wave functions were expanded by a plane-wave basis set with the cutoff energy of 450 eV, and the atomic relaxation was continued until the Hellmann-Feynman force acting on every atom became lower than  $0.01 \text{ eV}/\text{\AA}$ . For the exchange correlation functional we use the rev-vdW-DF2 method [31] which includes van der Waals (vdW) interactions and is known to be suitable for the layered transition metal dichalcogenides in predicting lattice parameters and atomic

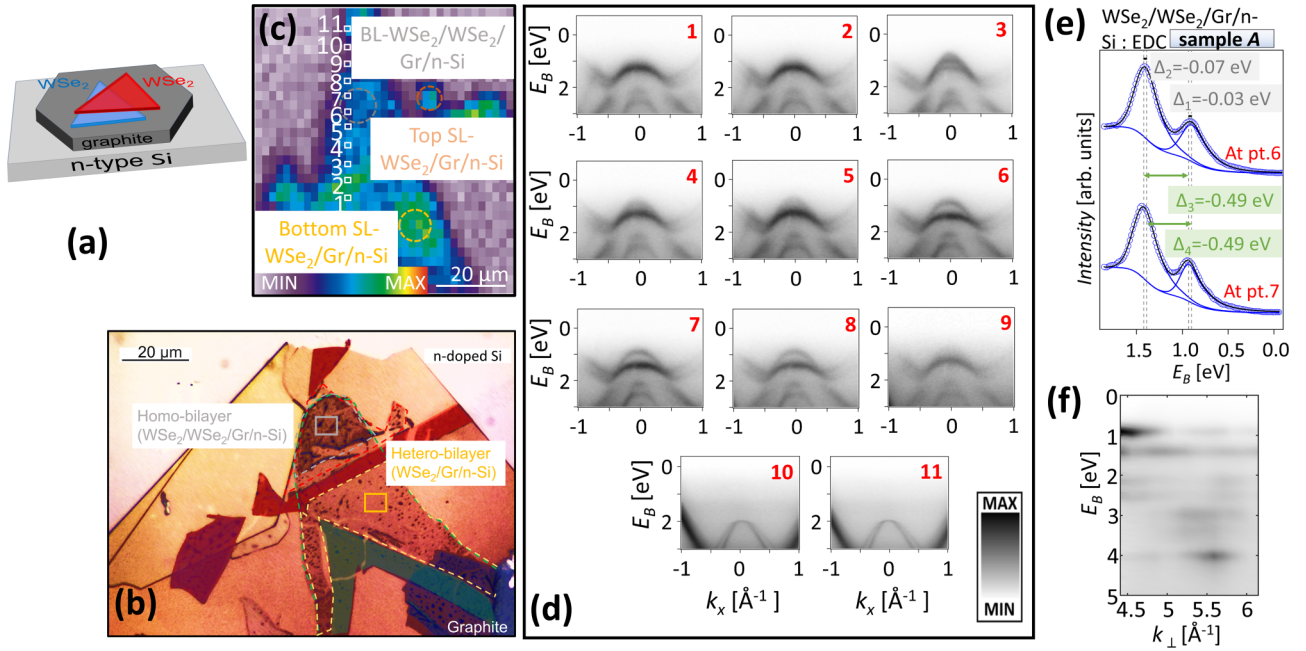


FIG. 1. Characterization of sample A. (a) Schematic model of the sample configuration. (b) Optical image and (c) spatial photoemission intensity map. (d) Set of normal emission ARPES maps at  $h\nu = 147$  eV at boxes indicated in (c). (e) Normal emission EDCs at boxes 6 and 7. (f)  $E_B(k_{\perp})$  map at box 7 made from set of normal emission EDCs for  $h\nu$  between 80 and 150 eV.

positions [32,33]. The Brillouin zone was sampled using the  $11 \times 11 \times 1$   $k$ -point grid for the primitive unit cell of 2H-WSe<sub>2</sub>. Band unfolding was performed using the method of Popescu and Zunger [34] as implemented in the VASPBAUM code [35].

Spin-orbit coupling (SOC) was taken into account in the calculation of the electronic structure, but ignored in the structural relaxations, where the impact was found to be negligible.

### III. RESULTS

#### A. Identification of SL and BL microregions

Figure 1(a) shows a schematic arrangement and Fig. 1(b) an optical micrograph of the sample A with the SL WSe<sub>2</sub> and twisted BL WSe<sub>2</sub> flakes on graphite at different twist angles. A graphite flake (exfoliated directly on a highly  $n$ -doped silicon wafer) serves as an atomically flat conducting substrate. The sample region where any portion of the top WSe<sub>2</sub> monolayer flake covers the bottom monolayer flake of WSe<sub>2</sub> is the BL region. The areas of the overlapping regions of twisted BL WSe<sub>2</sub>/graphite and twisted SL WSe<sub>2</sub>/graphite flakes are denoted by the gray and yellow dotted lines in Fig. 1(b). Figure 1(c) has been measured by scanning the microfocused beam of photons over the sample surface at a photon energy of 147 eV and measuring photoelectrons emitted from the valence bands at the momenta related to WSe<sub>2</sub>. It identifies the same region as shown in the optical image in Fig. 1(b). A similar micrograph from the sample B is presented in the Supplemental Material, Fig. S1 [36].

Figure 1(d) depicts a set of ARPES maps at 11 boxes indicated in Fig. 1(c), demonstrating that the microfocused beam spot can precisely select the desired area on the sample, clearly distinguishing between SL [boxes 1 and 2 in Fig. 1(c),

single band at the VBM at  $\Gamma_0$ ], BL (boxes 6–8, double band at  $\Gamma_0$ ), and graphite (boxes 10–11) regions. The double band near the VBM at  $\Gamma_0$  results from the bonding-antibonding interaction between  $d_{z^2}$  and  $p_z$  orbitals from the adjacent layers, and is a signature of a BL. Respectively, a single band is a signature of a SL. In Fig. 1(e) we show Voigt fits of the normal emission energy distribution curves (EDCs) from boxes 6 and 7 and identify binding energy shifts of the order of 30 meV. This suggests inhomogeneities and local doping varying on the  $\mu\text{m}$  scale on the flake surface within the BL region. The average splitting between bonding and antibonding states at  $\Gamma$  is between 0.48 and 0.52 eV at different positions of samples A and B. These values are significantly smaller than  $\sim 0.6$  eV in nontwisted BL WSe<sub>2</sub> [3,24,37,38], which suggests reduced hybridization in our twisted layers.

Figure 1(f) shows the  $E_B(k_{\perp})$  map at the BL region made from normal emission EDCs for  $h\nu$  between 80 and 150 eV, with the perpendicular momentum  $k_{\perp} = \sqrt{(E_{\text{kin}} + V_0)2m/\hbar^2}$ , and  $V_0$  set to 10 eV. The bonding-antibonding features near the local VBM at  $\Gamma_0$  ( $E_B$  near 1 and 1.5 eV) are present at all probed  $k_{\perp}$ . Furthermore, these states exhibit the expected intensity modulation due to the final-state interference (the matrix element effect), with no other states appearing in this range, indicating that we are exclusively probing the BL region. Qualitatively, the mechanism of this modulation can be explained through a free-electron final-state ARPES model [39], where the normal emission free-electron final-state (FEFS) matrix element  $\langle e^{ik_{f\perp} \cdot z} | \Psi \rangle$  for the two hybridized layers separated by the distance  $d$  is modulated by the factor  $1 + e^{ik_{\perp} \cdot d}$ . This will be additionally modulated when taking into account the radial part of the orbital wave function and selection rules [39], while an accurate description of the

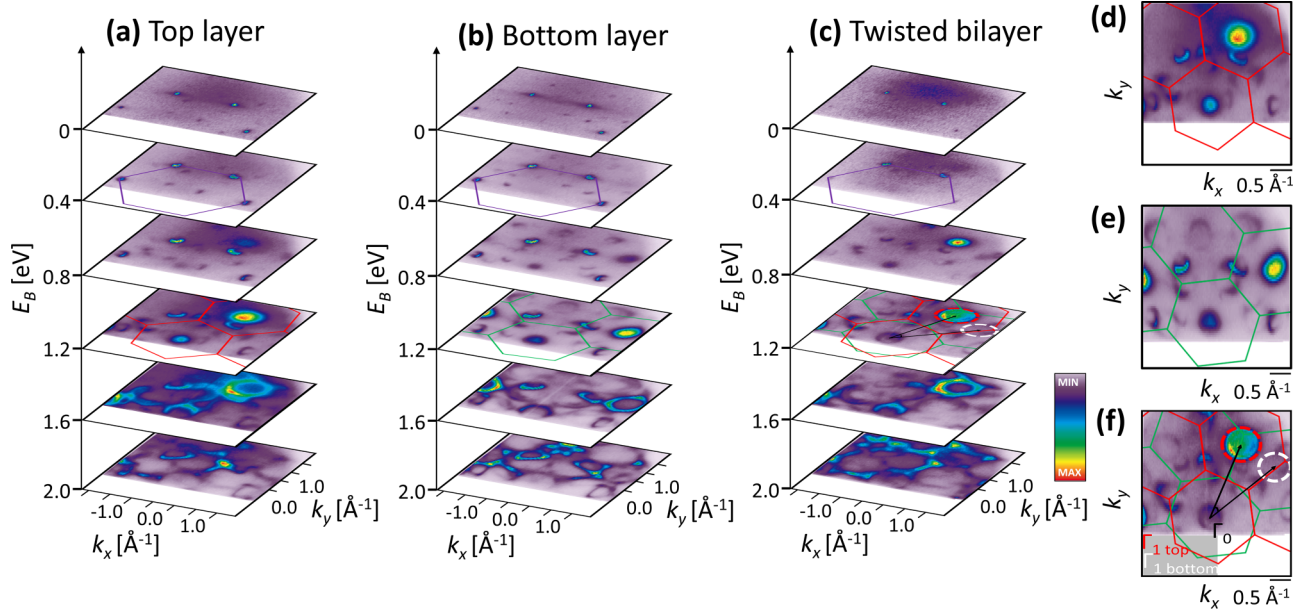


FIG. 2. ARPES spectra from WSe<sub>2</sub> SLs and BL of sample *B*. (a), (b) Show maps from top and bottom SLs, and (c) from the BL. (d)–(f) Show details of the maps for top SL, bottom SL, and BL, respectively, at  $E_B = 1.2$  eV. Red and white dashed circles in (f) represent the positions of the  $\Gamma_1$  from top and bottom layers, and black arrows depict the twist angle.

photoemission process is more complex and uses the time-reversed LEED final state [40].

### B. 3D ARPES data sets

Figure 2 shows an overview of  $I(E_B, k_x, k_y)$  data sets from sample *B*. The extended measured angular range allows imaging both  $\Gamma_0$  (center of the first surface BZ,  $k_x = k_y = 0$ ) and  $\Gamma_1$  (second BZ) points of WSe<sub>2</sub> in a single map. The lower binding energy region shows  $K_{gr}$  points of the graphite substrate, depicted by hexagons in maps at  $E_B = 0.4$  eV in Figs. 2(a)–2(c). The binding energy region at  $E_B = 0.8$  eV and higher contains a mixture of graphite and WSe<sub>2</sub> bands, and in maps at  $E_B = 0.8$  eV we identify first and second BZs of the WSe<sub>2</sub> layers through their respective  $\Gamma$  points.

Similar maps for sample *A* are shown in Fig. 3. The details of the  $\Gamma_1$  region for the BL WSe<sub>2</sub> of sample *A* are shown in Fig. 4. A faint intensity related to the  $\Gamma_1$  hole pocket of the bottom WSe<sub>2</sub> layer can be identified in Fig. 3(c), and is depicted by the white circle in Fig. 3(d). The intensity ratio between top and bottom layer  $\Gamma_1$  features is  $\sim 5/1$ , suggesting an inelastic mean-free path of  $< 1$  nm for WSe<sub>2</sub> valence electrons at our photon energy of 147 eV. Figures 4(c)–4(e) show the  $E_B(k_x)$  cuts through the  $\Gamma_1$  points of the top and bottom WSe<sub>2</sub> layers. In Fig. 4(d) the faint shadow related to the hole pocket of the bottom WSe<sub>2</sub> layer can be identified, and it is depicted by the white dotted line in Fig. 4(e). Neither of these maps show the indications of the flat band formations due to the moiré potential of the twisted BL.

Figures 2(d)–2(f) show details of the maps at  $E_B = 1.2$  eV. Due to the lack of inversion symmetry, this results in a trigonal symmetry of the WSe<sub>2</sub> monolayer; the intensity of  $\Gamma_1$  points at neighboring BZs is strongly modulated, with the signal

from every second  $\Gamma_1$  nearly vanishing. This effect is similar to trigonal low-energy electron diffraction (LEED) patterns measured on single-terrace terminations from TMDCs [41]. Interestingly, since the effect is observed in a SL, it indicates that it derives from the direction of the topmost W–Se bonds through the surface sensitivity of ARPES. Since the topmost valence bands at  $\Gamma$  derive almost exclusively from the  $d_{z^2}$  orbitals localized on W sites and  $p_z$  orbitals localized on Se, the effect can be explained by interference within the FEFS matrix element  $\langle e^{i\mathbf{k}_f \cdot \mathbf{r}} | \Psi \rangle$ , with positions  $\mathbf{r}$  of W and Se sites reflecting the lack of the inversion symmetry, and leading to different phase shifts in the matrix element [42]. However, for a quantitative description one would need to consider a more complete final state.

We can utilize the clear trigonal symmetry of the constant energy maps (CEMs) to unambiguously assign the twist angle as visualized in Figs. 2(f) and 3(d) for samples *B* and *A*, respectively. The detailed analysis is presented in the Supplemental Material, Sec. SV [36], and yielded  $\sim 28^\circ$  for sample *B* and  $\sim 10^\circ$  for sample *A*. We estimate the accuracy of the twist angle estimation angle from hemispherical analyzer CEMs to be  $\pm 1^\circ$  with the uncertainty dominated by intrinsic nonlinearities in the angular scale, in particular with the wide-angle mode ( $\sim 36^\circ$ ) used in this work. These issues originate mostly in the analyzer lens system, and are difficult to correct systematically. We will further discuss them in the later part of the paper.

### C. Orbital character and VBM estimation

Figure 5 shows the calculated band structures of a freestanding SL, and aligned AA' (derived from bulk 2H polytype) and AA (with layers on top of each other) stackings [17,43] for a BL WSe<sub>2</sub>. The topmost valence bands are a mixture of out-of-plane  $d_{z^2}$  and  $p_z$  orbital characters at  $\Gamma$  and

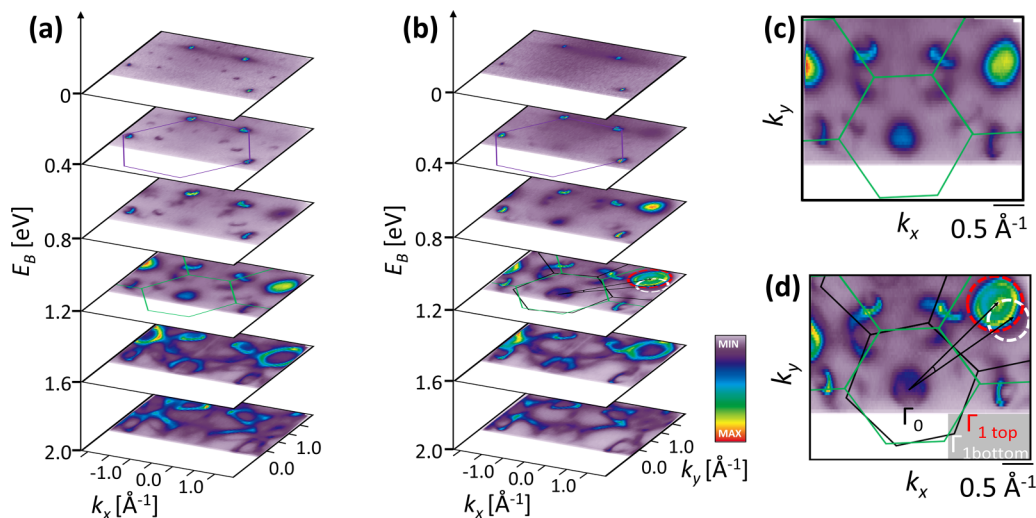


FIG. 3. ARPES spectra from WSe<sub>2</sub> SLs and BL of sample A. (a) Shows the maps from the bottom SL and (b) from the BL. (c), (d) Show details of the maps from bottom SL and BL, respectively, at  $E_B = 1.2$  eV. Red and white dashed circles in (d) represent the positions of the  $\Gamma_1$  from top and bottom layers, and black arrows depict the twist angle.

a mixture of in-plane  $d_{x^2-y^2}$  and  $d_{xy}$  orbital characters at  $K_W$ . Figure 6 shows selected maps from the twisted BL of sample B measured with  $p$ - [top row, panels (a)–(c)] and  $s$ -polarized light [bottom row, panels (d)–(f)]. As expected, the bands near  $\Gamma_0$  are more intense for  $p$ -polarized light, due to their out-of-plane orbital character [Fig. 6(b)]. Conversely, bands at  $K_W$  are more pronounced for  $s$ -polarized excitation [Fig. 6(f)]. The VBM of a 2H-stacked BL is at  $K_W$  [3], therefore, in the twisted BL, where the interaction between the layers is weaker, the VBM is also expected at  $K_W$ . This is indeed the case, as seen from comparing Figs. 6(b) and 6(f). The splitting between the bands at the  $K_W$  point is  $\sim 0.48$  eV in agreement

with the previous studies [3,24,44], where values between 0.47 and 0.5 eV were obtained.

Figure 7(a) shows the same map as Fig. 2(d), where the graphite Dirac cone bands are located in the vicinity of the  $\Gamma_1$  of SL WSe<sub>2</sub>. We have focused on this region since the graphite Dirac bands are made from C  $2p_z$  and topmost WSe<sub>2</sub>  $\Gamma$  bands from W  $5d_z^2$  and Se  $4p_z$  orbitals that could potentially hybridize, leading to avoided crossings. Previously, such avoided crossings were proposed in monolayer graphene on MoS<sub>2</sub> [45] and in SL MoS<sub>2</sub>/graphene [25] through the analysis of the second derivative microARPES spectra. Within our experimental resolution, we observe no sign of such hybridization since the dispersion of the WSe<sub>2</sub>  $\Gamma_1$  band is unaffected in the region where it crosses with the graphite Dirac band. We took advantage of the “dark corridor” of the Dirac bands [46], where the spectral intensity of one of the Dirac band branches is essentially turned off. This avoids having an incoherent intensity sum the two bands, allowing to inspect any modification of the  $\Gamma_1$  band separately.

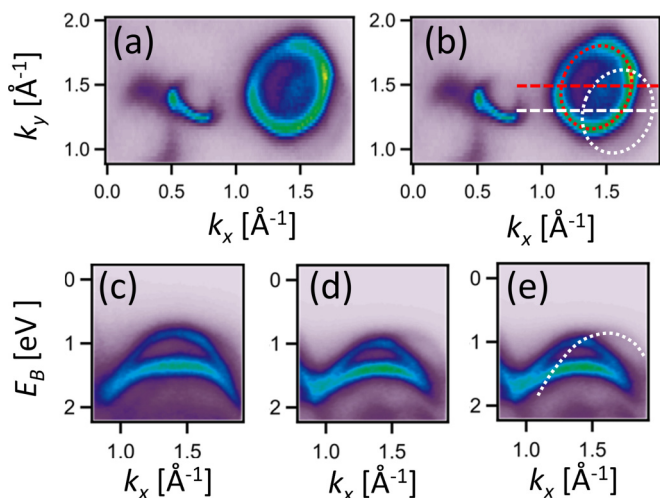


FIG. 4. (a) Details of the spectra from sample A near the  $\Gamma_1$  at  $E_B = 1.14$  eV. (b) Same map as in (a) but with red and white circles indicating the positions of  $\Gamma_1$  from top and bottom layers, respectively. (c), (d)  $E_B(k)$  cuts along the red and white dashed lines indicated in (b), respectively. (e) Same as (d) but with the guide line indicating the dispersion of the bottom layer  $\Gamma_1$  band.

#### D. Copies of graphite $K$ -point Dirac cones

The Fermi surface maps in Figs. 2 and 3 show a set of dotlike features which stem from the graphite Dirac conelike dispersions. These maps are shown in detail in Fig. 8, where one can see a set of intense dots related to graphite  $K_{gr}$  point and additional weaker dots which we attribute to their copies. When the electrons emitted from graphite are passing through the WSe<sub>2</sub> monolayer, they can be diffracted leading to first- and higher-order copies in the CEMs. These copies shall appear for all graphite bands, but they are most pronounced near the Fermi level, where  $K_{gr}$  points are sharp and no other bands are present. Copies are further characterized to demonstrate their conical dispersion through the CEM at  $E_B = 1$  eV [Fig. 8(e)] and comparison between the  $E(k)$  map at the zero-order graphite  $K_{gr}$  point [Fig. 8(f)] and one of the first-order copies [Fig. 8(g)]. Another case of such diffraction copies has been discussed by Ulstrup *et al.* [19] for a similar

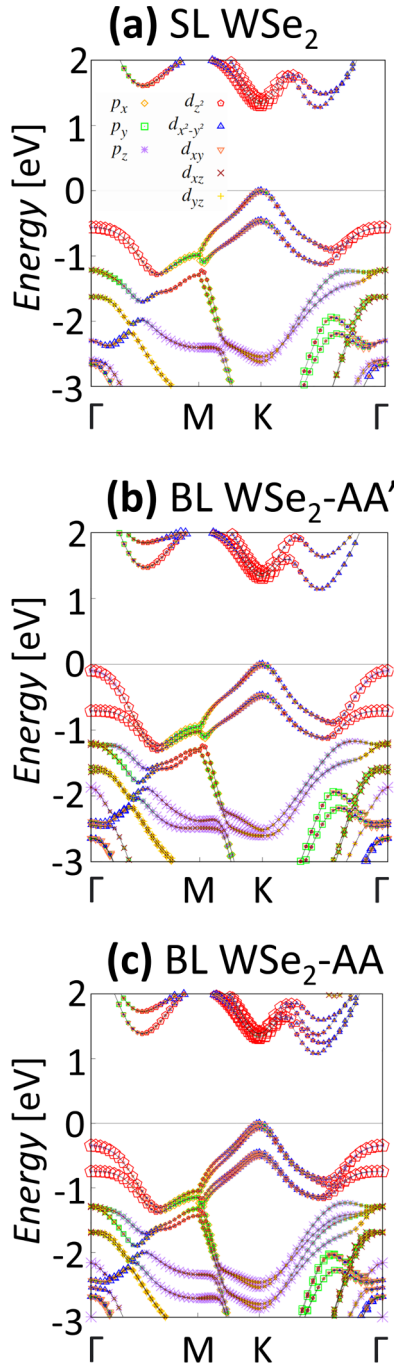


FIG. 5. Calculated orbital characters for the (a) freestanding SL, (b) AA' (2H) BL, and (c) AA BL WSe<sub>2</sub> [17]. The symbols associated with various orbital characters for Se (*p*) and W (*d*) are explained in (a).

interface of graphene/WS<sub>2</sub>. Compared to our WSe<sub>2</sub>/graphite interface, in their case the sequence of layers is reversed, hence, electrons emitted from WS<sub>2</sub>  $\Gamma_0$  have been diffracted through the graphene layer.

Mathematically, the wave vectors of the copies can be computed through the reciprocal space vectors of participating layers  $\mathbf{G}_W$  and  $\mathbf{G}_G$  for WSe<sub>2</sub> and graphite, respectively. We define the twist angle between graphite and WSe<sub>2</sub> as  $\theta = \arccos(\frac{\mathbf{G}_W \cdot \mathbf{G}_G}{|\mathbf{G}_W| |\mathbf{G}_G|})$  and the moiré vector  $\mathbf{G}_m = \mathbf{G}_W - \mathbf{G}_G$ .

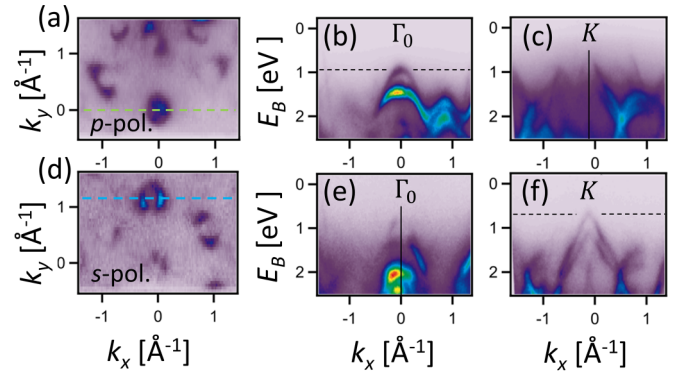


FIG. 6. Selected maps from the BL of sample *B*. Top row (a)–(c) CEM at  $E_B = 1$  eV for *p*-polarized light. Bottom row (d)–(f) CEM at  $E_B = 1$  eV for *s*-polarized light. Green dashed line in (a) shows the momentum trajectory for maps (b) and (e). Blue dashed line (d) shows the momentum trajectory for (c) and (f). Black dashed lines in (b) and (f) indicate the local VBM at  $\Gamma_0$  and *K* points, respectively.

Following Ref. [19] we obtain the angle of the copies as  $\phi_m = \arctan(\frac{\sin \theta}{\cos \theta - |\mathbf{G}_G|/|\mathbf{G}_W|})$  and the length of their vectors  $|\mathbf{G}_m| = \frac{G_G^2 - |\mathbf{G}_G| |\mathbf{G}_W| \cos \theta}{|\mathbf{G}_G| \cos \phi_m}$ .

Figures 8(a)–8(d) show the CEMs near the Fermi level ( $E_B = 30$  meV) for the *bottom* and *top* SL WSe<sub>2</sub> structures of sample *B* (*bottom* and *top* refer to the monolayers forming the BL WSe<sub>2</sub> [see Figs. 2(a) and 2(b)]. Figures 8(b) and 8(d) show the same data as 8(a) and 8(c), respectively, but with added simulated positions of the Dirac point copies according to the above equations. The first-order diffraction creates six copies around each  $K_{gr}$  point of graphite, at a reciprocal distances of  $\mathbf{G}_W$ . Some of these  $\mathbf{G}_W$  vectors are plotted in Fig. 8(h) to clarify the arrangement of copies near the zone center in Fig. 8(d). Interestingly, in Fig. 8(d) only three out of these six copies can be identified, which we attribute to the lack of inversion symmetry in WSe<sub>2</sub> and the directional bonds, as discussed earlier. We have used  $\theta_{WG} = 7^\circ$  for the *bottom* SL [Fig. 8(b)] and  $\theta_{WG} = 24^\circ$  for the *top* SL [Fig. 8(d)] to obtain the best overall match with the experiment. We note that the sum of these angles adds to  $31^\circ$ , which does not agree with  $\theta = 28^\circ$  determined from Figs. 2(d)–2(f). This is related to the problems in determination of twist angle from the CEMs measured by the hemispherical analyzer, as discussed below.

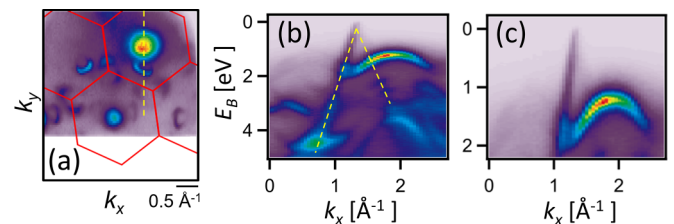


FIG. 7. Crossing between  $\Gamma_1$  and graphite bands in sample *B*. (a) CEM at  $E_B = 1.2$  eV; yellow dashed line shows the BZ trajectory for maps (b) and (c). (b)  $E(k_y)$  showing the region where graphite and  $\Gamma_1$  band cross; yellow dashed line depicts the graphite Dirac cone dispersion. (c) Magnified region of the crossing.

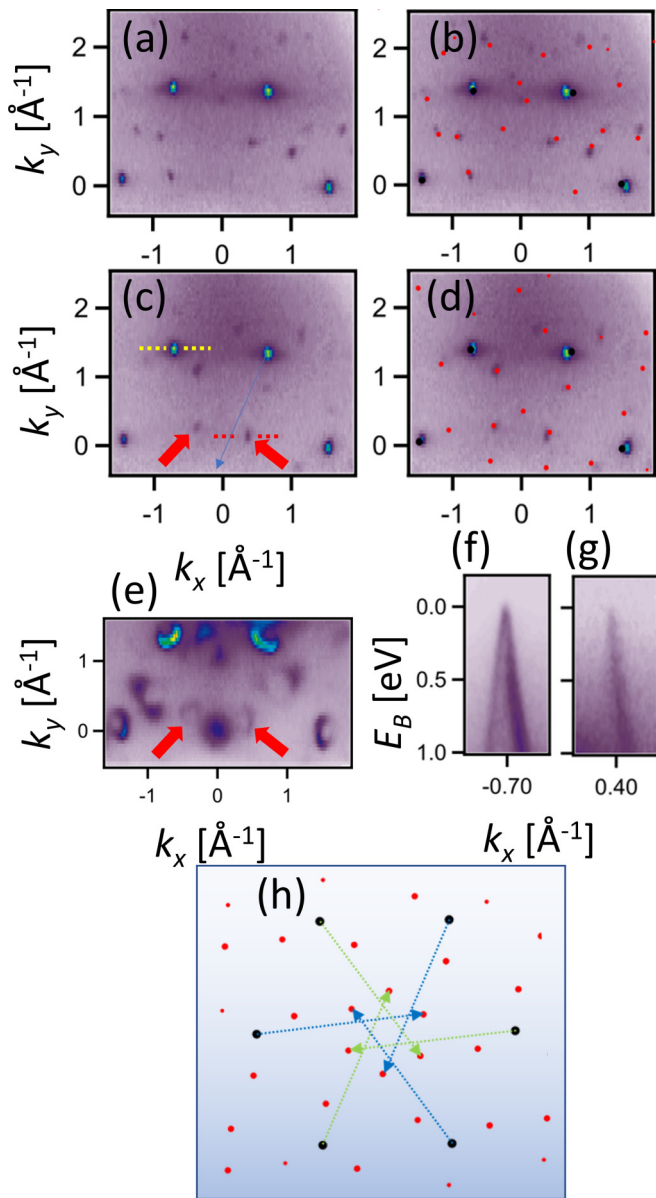


FIG. 8. (a), (b) Fermi level CEMs ( $E_B = 30$  meV) for the bottom SL WSe<sub>2</sub>/graphite in sample *B*. (c), (d) Same for the top SL WSe<sub>2</sub>/graphite in sample *B*. (e) CEM for the top SL WSe<sub>2</sub>/graphite at  $E_B = 1$  eV. (f), (g) Show  $E_B(k_x)$  maps of zero-order graphite  $K$  point and one of the copies along the trajectories indicated, respectively, by yellow and red dashed lines in (c). Red arrows in (c) and (e) identify selected copies of graphite  $K$  points, confirming conical shapes of their dispersions. (h) Arrangement of copies related to (d) with indicated  $\mathbf{G}_W$  vectors of SL WSe<sub>2</sub>. Different colors of the arrows reflect the trigonal symmetry of SL WSe<sub>2</sub>.

Closer inspection of Figs. 8(b) and 8(d) reveals small discrepancies between the experimental and computed positions of the Dirac copies. We argue that this is related to the nonlinearities of the angular scale in the hemispherical analyzer 2D multi-channel plane (MCP) detector, which might be further influenced by a slight off-axis misalignment of the photon beam spot with respect to the analyzer lens axis. These effects directly translate into momentum scale nonlinearities. ARPES maps can also be measured by an alternative spectrometer

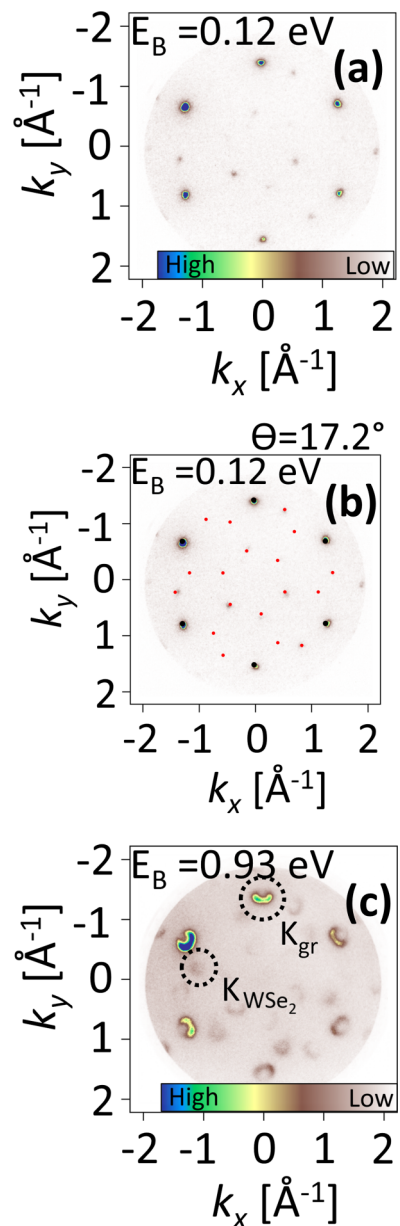


FIG. 9. Maps measured on sample *C* at the NanoESCA beam line with *p*-polarized light at  $h\nu = 40$  eV at 80 K. (a) CEM of SL WSe<sub>2</sub>/graphite at  $E_B = 0.12$  eV. (b) Same as (a) but overlaid with Dirac copies calculated for 17.2° twist angle between WSe<sub>2</sub> and graphite. (c) CEM at  $E_B = 0.93$  eV, indicating the  $K$  points of graphite and WSe<sub>2</sub>.

design, the so-called *momentum microscope* [47]. In a momentum microscope, the rotational symmetry of the reciprocal space around the sample surface normal is faithfully reproduced through the cylindrical symmetry of the spectrometer lens (due to the momentum microscope design, there is a small binding energy shift of 20–50 meV, in our case along  $k_y$  [48], which in principle can be corrected, but has been neglected here). We have performed momentum microscopy at the NanoESCA beam line at Elettra synchrotron on sample *C* which contained SL WSe<sub>2</sub> flake of 20- $\mu$ m lateral size on graphite (details on sample *C* are in the Supplemental

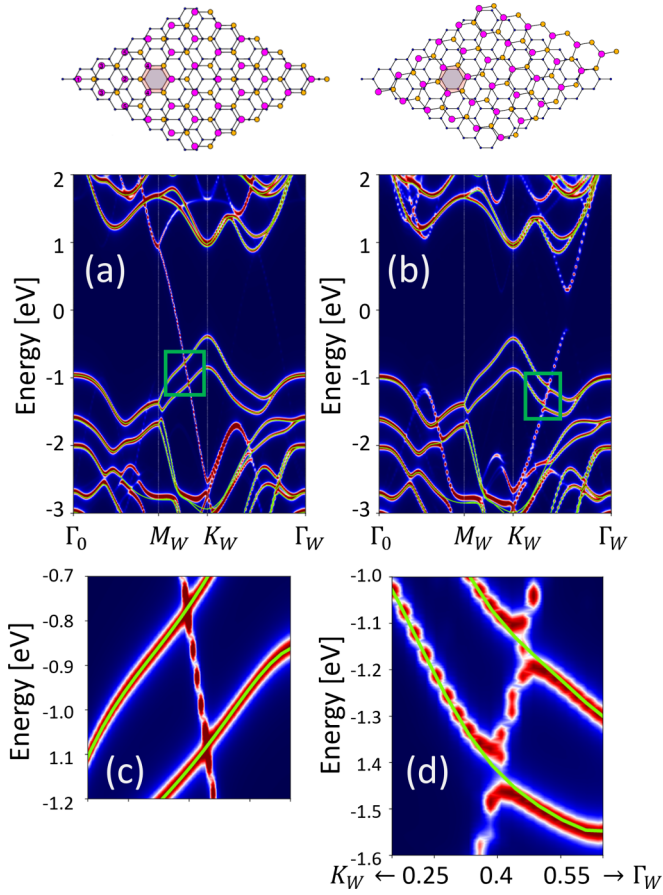


FIG. 10. Theoretical calculations for aligned (a) and  $21.79^\circ$  twisted (b) SL WSe<sub>2</sub> on graphene. The theoretical band structure is deconvoluted onto the Brillouin zone of the freestanding SL WSe<sub>2</sub>. (c) and (d) show magnified areas of the green boxes in (a) and (b), respectively. Green lines (in all panels) show the band structure of a freestanding SL WSe<sub>2</sub>, for comparison.

Material, Sec. SIII [36]). It was essential to prepare such large flake due to the photon beam spot of 15–20  $\mu\text{m}$  diameter at the NanoESCA beam line. Figure 9 shows the momentum microscope maps from sample C. One can see that the overall fitting of the Dirac copies is more accurate as compared to Fig. 8, and allows us to establish the twist angle of  $\sim 17.2^\circ$  between graphite and SL WSe<sub>2</sub> in sample C. Again, the arrangement of copies has a trigonal symmetry, in contrast to zero-order  $K_{gr}$  points, which have a hexagonal symmetry.

### E. Theoretical calculations of twisted structures

Figure 10 shows theoretical calculations (with SOC included) for the heterobilayer structure (WSe<sub>2</sub>/graphene) with  $0^\circ$  and  $21.79^\circ$  hexagonal supercells. The ratio of the experimental WSe<sub>2</sub> to graphene lattice constants is very close to  $\frac{4}{3}$ , with only  $\sim 0.5\%$  mismatch. Therefore, we modeled the WSe<sub>2</sub>/graphene heterostructure containing a  $3 \times 3$  WSe<sub>2</sub> and a  $4 \times 4$  graphene supercell [49]. The common lattice constant of this heterostructure is 0.08% larger than freestanding graphene and 0.22% smaller than WSe<sub>2</sub> if the relaxed DFT values are compared. The twisted unit cells are constructed in terms of this common lattice parameter. The 2:1 ratio of the

unit vectors gives the twist angle of  $21.79^\circ$ , we define it as  $(m, n) = (1, 2)$ . A single layer of graphene approximates our experimental graphite substrate.

As shown in Figs. 10(a) and 10(b) for both aligned ( $0^\circ$  twist angle) and twisted ( $21.79^\circ$  twist angle) SL WSe<sub>2</sub>/graphene, there are only minor differences in band positions, as compared to the freestanding SL WSe<sub>2</sub> (green lines), in particular in the region near the VBM. Figure 10(c) shows a magnified region where SL WSe<sub>2</sub> and graphene bands cross for the case of  $0^\circ$  twist angle, where one can see band crossings without significant hybridization gaps. Figure 10(d) shows a similar region, but for the case of  $21.79^\circ$  twist angle. In this case hybridization gaps of the order of 50 meV can be resolved. This finding is probably related to the character of WSe<sub>2</sub> bands at momenta where they cross the graphene band. As shown in Fig. 5(a), the band character changes from in plane at the  $K$  point into out of plane at  $\Gamma$ . In case of Fig. 10(b) the crossing is further away from the  $K$  point [as compared to Fig. 10(a)], suggesting less in-plane character, more hybridization, and larger hybridization gaps. This process is competing with the interlayer distance, which is larger for the twisted SL WSe<sub>2</sub>/graphene.

Different stacking sequences in the WSe<sub>2</sub> BL have been considered in previous work [17,43]; however, aside from the previously defined AA' and AA, their nomenclature appears inconsistent. SL WSe<sub>2</sub> has a threefold rotation axis,  $C_3$ , without inversion symmetry, therefore, it has polarity in the in-plane direction (along the  $\Gamma M$  reciprocal direction). For the bilayer, in the aligned case, there are two general options: either the polarities of the adjacent layers face either in the same direction (such as in the 3R bulk polytype) or in opposite directions (the 2H bulk polytype). During the natural growth process, the in-plane shift between the layers is naturally adjusted; however, in the twisted structures it becomes an additional parameter. One can also imagine that at a very small twist angle, the twisted BL will contain large regions of stackings which differ only by that shift, and that the regions of energetically favorable stacking will become larger due to the atomic relaxation.

We focus on the AA and AA' stackings as starting points for modeling twisted bilayers, with the AA' stacking being the same as in the most stable 2H polytype, and AA being the two layers directly stacked on top of each other. Starting with AA we considered situations when twisting is either around the center of the W-Se hexagon, around W atoms, or around Se atoms (considering the top view of a BL). Starting with AA' we only considered twisting around the center of the W-Se hexagon. We define  $(m, n)$  and  $(n, m)$  as the unit vectors from the top and bottom WSe<sub>2</sub> layers, respectively, that make up the moiré unit cell. This relates to the twist angle  $\theta$  through  $\cos \theta = \frac{1}{2} \frac{m^2 + n^2 + 4mn}{m^2 + n^2 + mn}$ .

We have relaxed the twisted BL WSe<sub>2</sub> structures defined above for several twist angles with the resulting total energy differences and structural information provided in Table I. To reduce the complexity, SOC was not included in these calculations. For the aligned layers, we find the difference  $\Delta E$  between the most energetically favorable and unfavorable stackings AA' and AA to be  $-40.25$  meV per W atom in the unit cell. Since the twisted structures contain regions of favorable and unfavorable stackings, their expected energy



TABLE I. The calculated total energies and interlayer distances of twisted BL WSe<sub>2</sub> for the stacking sequence where twisting is around the center of in-plane WSe<sub>2</sub> hexagons. In these calculations SOC was not included.  $N_W$  is the number of W atoms per moiré unit cell.  $\Delta E$  is the energy difference between the AA stacking rotated around the center of the hexagon, as compared to the aligned AA ( $\theta = 0$ ) stacking;  $\Delta E = E(\text{AA}) - E_{t,\text{hex}}(\text{AA})$ .  $\Delta E_{t,\text{hex}} = E_{t,\text{hex}}(\text{AA}') - E_{t,\text{hex}}(\text{AA})$  is the energy difference, between the twisted AA' and AA stackings with the rotation axis at the center of the hexagon. The energies are given in meV per W atom. The structural parameters (in Å) are given for AA' stacking twisted around the center of the W-Se hexagon:  $\bar{d}_{W-W}$  is the average interlayer out-of-plane distance (along  $z$  axis) between W atoms, while  $\Delta d$  is the maximum out-of-plane difference of W atom positions within the layer, it represents the corrugation due to formation of the moiré pattern.

$\theta$	$N_W$	$(m, n)$	$\Delta E$	$\Delta E_{t,\text{hex}}$	$\bar{d}_{W-W}$	$\Delta d$
21.79°	14	(2,1)	18.50	-0.04	6.839	0.003
13.17°	38	(3,2)	18.73	-0.10	6.842	0.017
7.34°	122	(5,4)	20.20	-0.43	6.814	0.077
6.01°	182	(6,5)	21.04	-0.58	6.813	0.104
3.89°	434	(9,8)	22.56	-0.76	6.768	0.132
0	2	(1,1)	0	-40.25	6.547	0

should be approximately halfway between those of aligned AA' and AA. This is indeed the case, however, as the twist angle becomes small, the energies,  $-\Delta E$ , become lower, probably due to extended regions of favorable stacking. The average interlayer distance  $\bar{d}_{W-W}$  is larger for larger twist angles, which is again probably related to the larger areas of energetically favorable stacking for smaller twist angles. Accordingly, the corrugation  $\Delta d$  due to the moiré pattern is smaller at larger twist angles.

We also investigated the energy differences  $\Delta E_{t,\text{hex}}$  for the layers where the starting stacking is AA or AA'. We find that the difference in energy is smaller for larger twist angles, with the structures starting from AA' always being more stable. At small twist angles it likely reflects the energy differences between 2H (AA') and 3R-like stackings which form the areas of favorable stacking.

Figures 11(a)–11(c) show the arrangement of BZs and theoretical band dispersions, with SOC included, for BL WSe<sub>2</sub> at the twist angle 13.17° with twisting around the center of the W-Se hexagon starting with the AA' stacking. Therefore, in absolute terms related to the experimental results of Figs. 2 and 3, the twist angle is  $\theta = 60^\circ - 13.17^\circ = 46.83^\circ$ . Our actual experimental system consists of BL WSe<sub>2</sub>/graphite; however, we omit graphite to reduce numerical complexity. The bands are deconvoluted onto the BZ of one of the layers. As compared to the bands of an aligned AA' BL WSe<sub>2</sub> shown by green line [see also Fig. 5(b)], the difference near the VBM is mainly in reduced bonding-antibonding splitting of the bands at  $\Gamma$  as indicated by the white rectangle in Fig. 11(b). Figure 11(c) shows the details of the region where anticrossing hybridizations are observed, with the local gaps of the order of 50 meV.

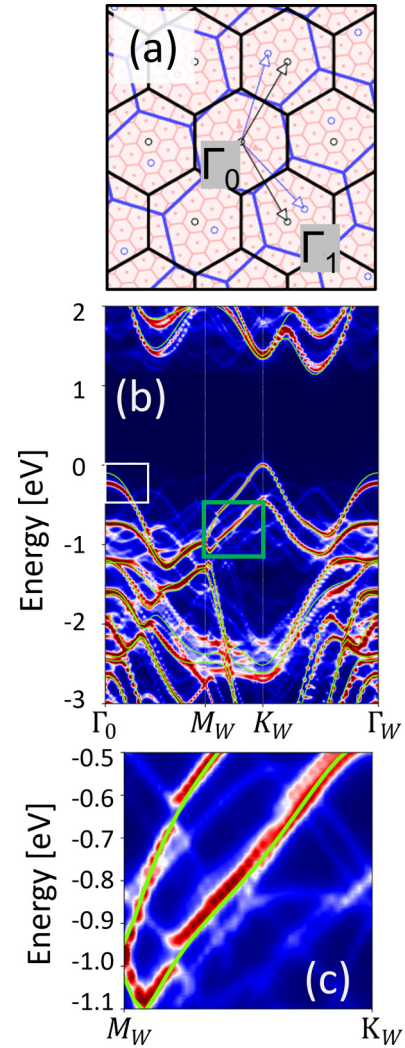


FIG. 11. Theoretical calculations for twisted BL WSe<sub>2</sub> at the twist angle  $\theta = 60^\circ - 13.17^\circ = 46.83^\circ$ . (a) Black and blue lines depict BZs of the two SLs and the network red lines the moiré BZs of the twisted layers. (b) Band structure unfolded onto the BZ one of the SL WSe<sub>2</sub>. (c) Magnified region depicted by the green rectangle in (b). For comparison, green solid lines show the bands for the 2H BL WSe<sub>2</sub>.

#### IV. DISCUSSION

We have performed band mapping on three different SL and two different BL WSe<sub>2</sub> samples placed on graphite. The flakes can be identified in microARPES by rastering the sample with a  $\sim 1 \mu\text{m}$  photon beam spot, and twist angles between the layers could be established from the CEMs. The hybridization between the WSe<sub>2</sub> and graphene for the twisted structure is predicted to depend on the orbital character of the bands at the crossing points, however, in experimental data no signatures of it could be identified in the uppermost region of valence bands. This might be related to the resolution of our ARPES data or to the increased interlayer distance in our WSe<sub>2</sub>/graphite structures, due to a particular twist angle or to impurities trapped between the layers. Accordingly, in the region of the upper valence bands, no dependence of the electronic dispersions on the twist angle between the WSe<sub>2</sub>

and graphite has been found, i.e., the spectral features reflect an incoherent sum of the graphite and ML WSe<sub>2</sub> bands. Previously, hybridization effects have been demonstrated for the interface between SL graphene and SL MoS<sub>2</sub> [25,45]; however, the effects were most pronounced at higher binding energies. Our theoretical results indicate that the hybridization may depend sensitively on the twist angle, which might be the reason for these discrepancies.

The electrons emitted from graphite near the Fermi level are focused in  $K_{gr}$  points, and we observe diffraction of these electrons when passing through WSe<sub>2</sub>. The arrangement of these replicas (sometimes called minibands [19]), which are basically umklapp transitions due to the WSe<sub>2</sub> lattice vectors, can be explained as a final-state effect that would be present also in noninteracting layers. Essentially the same process is expected when shooting the electron beam through a freestanding SL WSe<sub>2</sub>. Accordingly, the intensity of the copies follows the trigonal symmetry of a monolayer, bearing similarities to the LEED scattering experiment. Therefore, the existence of such band replicas is an indication of neither a hybridization between the layers nor a moiré-induced potential.

The bonding-antibonding gap at  $\Gamma$  that is a signature of WSe<sub>2</sub> interlayer hybridization persists in our twisted BL WSe<sub>2</sub> microflakes. Its large energy scale of  $\sim 0.4$  eV is in stark contrast to negligible hybridization between these bands near  $\Gamma$  from top and bottom layers, as demonstrated in Fig. 4. This is likely related to directional character of the participating Se  $p_z$  orbitals that form out-of-plane  $\sigma$ -like bonds but any interlayer in-plane hopping between these out-of-plane orbitals (which can be imagined as  $\pi$  like) is inhibited. Conversely, the in-plane orbital character at  $K_W$  points would allow interlayer in-plane  $\sigma$ -like hopping, but this interaction is inhibited by the large interlayer distance of these orbitals that are primarily located on a transition metal.

No indication of flat bands is present in our experimental ARPES maps and our calculations for twisted BL WSe<sub>2</sub> do not indicate any flat bands that are split off from the band structure of separate SLs. For moiré cells larger than in our calculations, recent calculations by Kundu *et al.* [17] identify flat bands over the  $\sim 50$  meV energy scale for twist angle up to  $5.1^\circ$ . Small twist angles lead to large moiré unit cells, and to large areas of relatively well-defined stacking areas, which exhibit significantly shifted band structures in the vicinity of  $\Gamma$ , as shown in Figs. 5(b) and 5(c). Our smallest experimental twist angle of  $\sim 10^\circ$  for BL WSe<sub>2</sub> of sample A is too large to allow for formation of experimentally observ-

able gaps between the bands, and in the experimental data small anticrossings might be smeared out. So far, no interlayer hybridization gaps have been reported in microARPES from twisted TMDCs, and the only potential indirect indication of the formation of a moiré potential is through the observation of multiple Dirac copies near the  $K_{gr}$  in the graphene/WS<sub>2</sub>/WSe<sub>2</sub> heterostructure [20].

In summary, we have described and examined properties of microARPES spectra from several twisted WSe<sub>2</sub> flake samples on graphite substrates. We established that the valence bands maximum of WSe<sub>2</sub> lies at  $K_W$  in all studied microstructures. Hybridization effects between twisted BL WSe<sub>2</sub> are manifested in the bonding-antibonding splitting at  $\Gamma$  that are readily observed in the experiment, but do not translate into further emergent interlayer hybridization gaps. Hybridization gaps are also not observed in the studied twisted SL WSe<sub>2</sub>/graphite structures. The Fermi level electrons emitted into the  $K_{gr}$  points diffract when passing through the WSe<sub>2</sub> overlayer, forming sharp replicas whose positions can be predicted by combining the reciprocal vectors of WSe<sub>2</sub> and graphite. Experimental findings are complemented by theoretical DFT modeling with the inclusion of vdW forces, which suggests that forming of hybridization in WSe<sub>2</sub>/graphene system sensitively depends on the orbital character of the WSe<sub>2</sub> at the crossing with the graphene Dirac cone band.

This work paves the way for designing future experiments on twisted TMDC bilayers at smaller twist angles, which would enable imaging their fascinating predicted properties such as topologically nontrivial flat bands.

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